

## AMENDMENTS TO THE CLAIMS

The claims in this listing will replace all prior versions, and listings, of claims in the application.

### Listing of Claims:

Claim 1. (Currently Amended) A light-emitting device formed by depositing p-type and n-type nitride semiconductor layers, comprising:

deposited p-type and n-type nitride semiconductor layers;  
semiconductor-surface-electrodes to apply currents into each of the semiconductor layers;  
an insulating layer which holds the semiconductor layers, said insulating layer comprising two surfaces; and

mount-surface-electrodes provided on one surface of the insulating layer which is opposite to the other surface of the insulating layer where the semiconductor-surface-electrodes are made;

wherein one of the semiconductor layers has a non-deposited area where the other semiconductor layer is not deposited;

one of the semiconductor-surface-electrodes is built up on the surface of the non-deposited area;

VIA's vias are made in the insulating layer which electrically connect ~~electrically~~ the semiconductor-surface-electrodes and the mount-surface-electrodes; ~~and~~

the semiconductor-surface-electrodes, the insulating layer, and the mount-surface-electrodes are built up in this order on one side of the deposited semiconductor layers; and

the other surface of the deposited semiconductor layers is used as light emitting surface and there are no obstacles such as a sapphire substrate or electrodes on the surface.

Claim 2. (Original) The light-emitting device of claim 1, wherein the insulating layer is made of one of resin, ceramics, or silicon.

Claim 3. (Currently Amended) The light-emitting device of claim 1, wherein the ~~VIA is~~ vias are filled with electric conductor.

Claim 4. (Currently Amended) The light-emitting device of claim 1, wherein phosphor is provided on ~~the~~ a surface or in ~~the~~ an interior portion of the semiconductor layer.

Claim 5. – Claim 18. (Canceled)